

Amendments to the Specification

Please replace the title with the following amended title:

A CAPACITOR AND A METHOD OF MANUFACTURING A CAPACITOR WITH
COPPER ELECTRODES AND DIFFUSION BARRIERS PROCESS THEREFOR

Kindly amend the specification as follows:

Page 1, between the title and the heading "**BACKGROUND OF THE
INVENTION**", insert

--CROSS REFERENCE TO RELATED APPLICATIONS

This is a divisional application of application Serial No. 09/685,586, filed October 11, 2000, which is hereby incorporated by reference in its entirety for all purposes.--

***Please replace the paragraph beginning on page 5, line 15 with the
following amended paragraph:***

In addition, on this interlayer insulating film 13, an interlayer insulating film 14 (14a, 14b and 14c) for multilevel interconnection are formed, and in the interlayer insulating film ~~[[13]]~~ 14, a capacitor 10 according to the present invention is formed.

Please replace the paragraph beginning on page 6, line 19 with the following amended paragraph:

An etching stopper film, in other words, a SiN film 15b on the lower layer 14a of the interlayer insulating film 14 is formed to cover the barrier 18b extending on the top surface of the lower electrode 17. Formed passing through this SiN film 15b and the SiN film 15c and the layers 14b and 14c of the interlayer insulating film 14 is a recess 19, in which a dielectric 24 ~~are~~ 20 is formed.

Please replace the paragraph beginning on page 13, line 8 with the following amended paragraph:

~~Fig. 2~~ Fig. 3 resembles the drawing in Fig. 1, but shows the second embodiment of the capacitor according to the present invention.

Please replace the paragraph beginning on page 21, line 13 with the following amended paragraph:

As shown in Fig. 8(b), the SiN film 15b on the lower insulating layer 14a is etched by photolithography and etching is the same manner as descried previously to remove specified portions to expose the lower electrode 17, and a barrier layer 18b is deposited on the exposed lower electrode 17 as shown in Fig. 8(c).